

**BAV70DW/BAV99DW/BAW56DW
BAV99BRW/BAV756DW/BAW567DW**

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BAV70DW/BAV99DW/BAW56DW BAV99BRW/BAV756DW/BAW567DW

150mA Surface Mount
Switching Diode Array - 100V

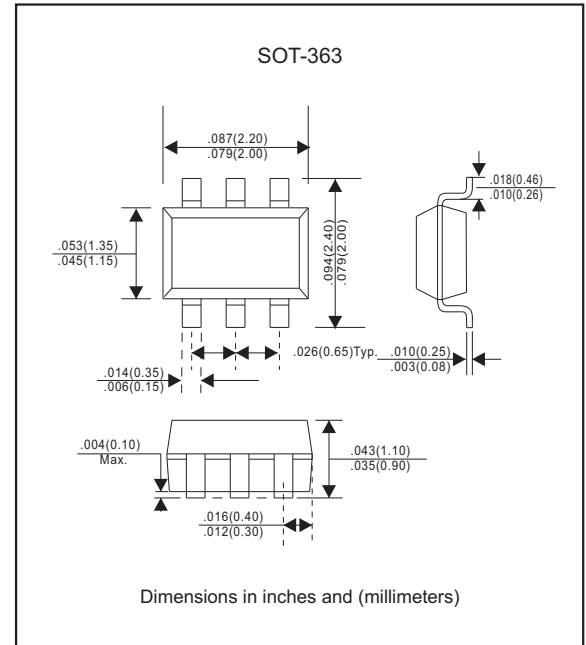
Features

- Fast speed switching.
- For general purpose switching application.
- High conductance.
- Easily connected as full wave bridge
- Silicon epitaxial planar chip.
- Lead-free parts meet RoHS requirements.
- Suffix "-H" indicates Halogen-free parts, ex. BAV70DW-H

Mechanical data

- Epoxy: UL94-V0 rated flame retardant
- Case : Molded plastic, SOT-363
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Mounting Position : Any
- Weight : Approximated 0.006 gram

Package outline



Maximum ratings (AT $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	Symbol	Limit	UNIT
Non-repetitive peak reverse voltage	V_{RM}	100	V
Peak repetitive reverse voltage	V_{RRM}	75	V
DC blocking voltage	V_R		V
RMS reverse voltage	$V_{R(RSM)}$	53	V
Forward continuous current	I_{FM}	300	mA
Average rectified output current (Note 1, 3)	I_O	150	mA
Non-repetitive peak forward surge current 8.3ms	I_{FSM}	2.0	A
Typical thermal resistance junction to ambient (Note 1, 3)	$R_{\theta JA}$	625	$^\circ\text{C}/\text{W}$
Power dissipation (Note 1, 3)	P_D	200	mW
Operating junction temperature range	T_J	-55 to +150	$^\circ\text{C}$
Storage temperature range	T_{STG}	-55 to +150	$^\circ\text{C}$

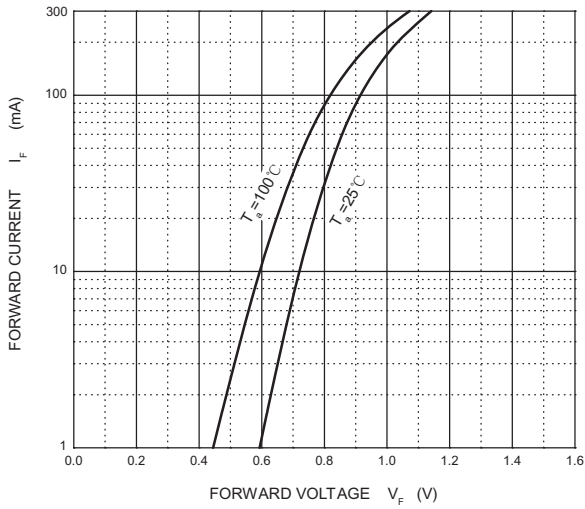
Electrical characteristics (AT $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	Symbol	Min	Max	UNIT
Reverse breakdown voltage	V_{BR}	75		V
Reverse leakage current (Note 2)	I_R	at $V_R = 75\text{V}$	2.5	μA
		at $V_R = 20\text{V}$	25	nA
Total capacitance, $V_R = 0\text{V}$, $f = 1.0\text{MHz}$	C_D		2.0	pF
Reverse recovery time, $I_F = I_R = 10\text{mA}$, $I_{RR} = 0.1 \times I_R$, $R_L = 100\Omega$	t_{rr}		4.0	ns
Forward voltage (Note 2)	V_F	at $I_F = 1.0\text{mA}$	715	mV
		at $I_F = 10\text{mA}$	855	
		at $I_F = 50\text{mA}$	1000	
		at $I_F = 150\text{mA}$	1250	

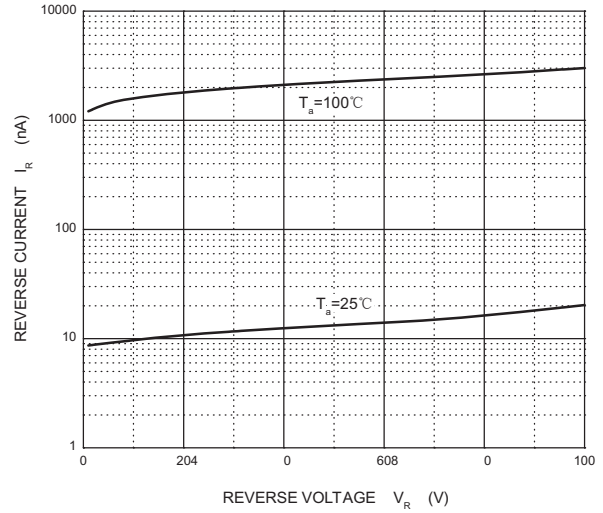
Notes 1: Device mounted on FR-4 PC board with recommended pad layout
 2: Short duration test pulse used to minimize self-heating effect.
 3: One or more diodes loaded.

Rating and characteristic curves for each diode (BAV70DW/BAV99DW/BAW56DW/BAV99BRW/BAV756DW/BAW567DW)

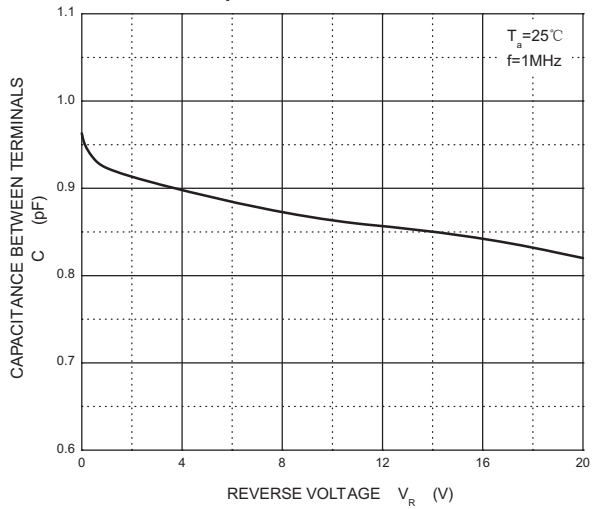
Forward Characteristics



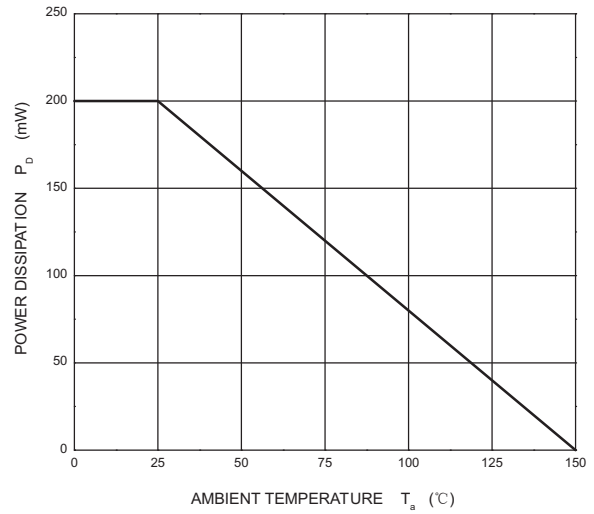
Reverse Characteristics



Capacitance Characteristics



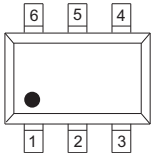
Power Derating Curve



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Pinning information

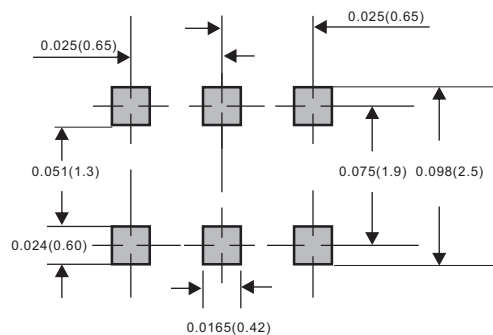
Simplified outline



Type number	Marking code	Symbol	Type number	Marking code	Symbol
BAV70DW	KJA		BAV99BRW	KGJ	
BAV99DW	KJG		BAV756DW	KCA	
BAW56DW	KJC		BAW567DW	KAC	

Suggested solder pad layout

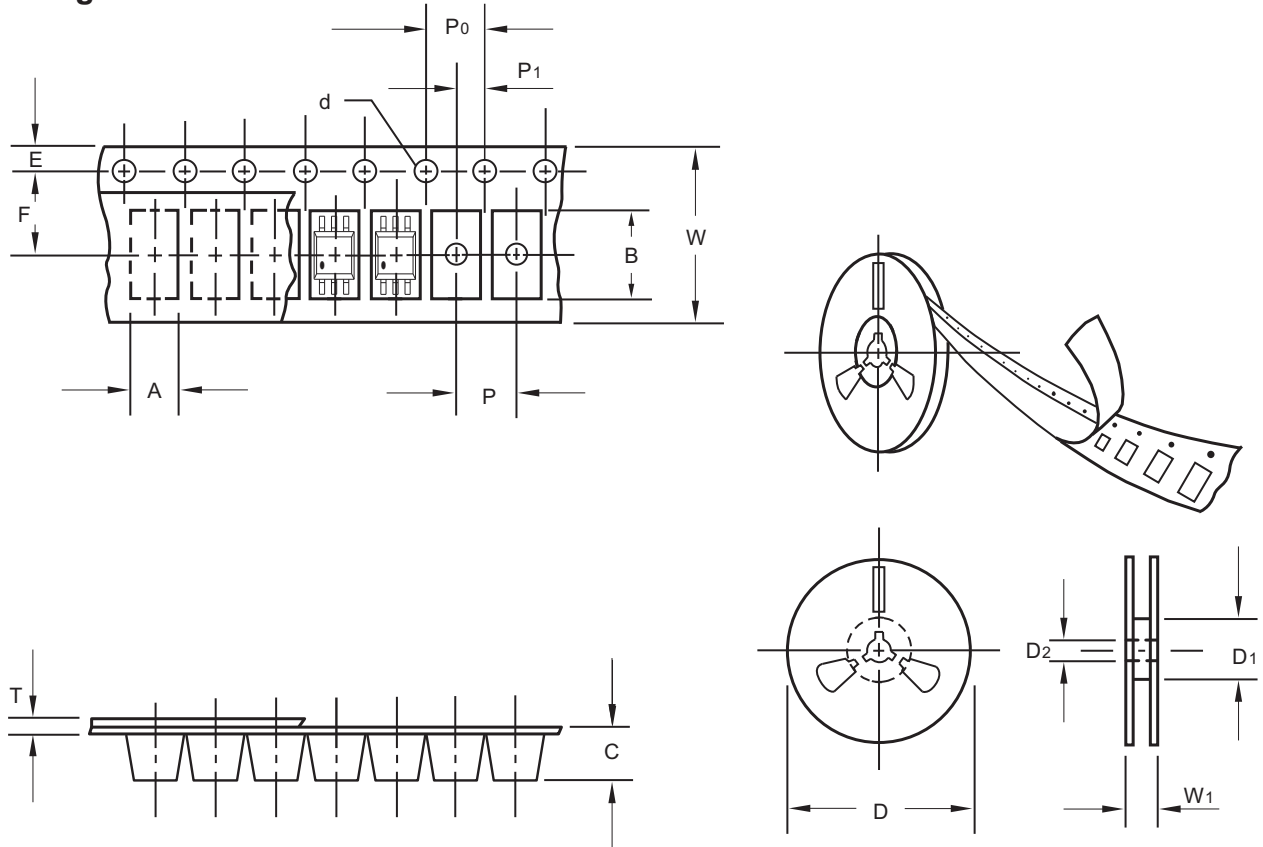
SOT-363



Dimensions in inches and (millimeters)

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Packing information



unit:mm

Item	Symbol	Tolerance	SOT-363
Carrier width	A	0.1	2.25
Carrier length	B	0.1	2.55
Carrier depth	C	0.1	1.20
Sprocket hole	d	0.1	1.50
13" Reel outside diameter	D	2.0	-
13" Reel inner diameter	D1	min	-
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D1	min	54.40
Feed hole diameter	D2	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	3.50
Punch hole pitch	P	0.1	4.00
Sprocket hole pitch	P0	0.1	4.00
Embossment center	P1	0.1	2.00
Overall tape thickness	T	0.1	0.23
Tape width	W	0.3	8.00
Reel width	W1	1.0	11.40

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.

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High reliability test capabilities

Item Test	Conditions	Reference
1. Solder Resistance	at 260±5°C for 10±2sec.	MIL-STD-750D METHOD-2031
2. Solderability	at 245±5°C for 5 sec.	MIL-STD-202F METHOD-208
3. High Temperature Reverse Bias	$V_R=80\%$ rate at $T_J=150^\circ\text{C}$ for 168 hrs.	MIL-STD-750D METHOD-1038
4. Forward Operation Life	Rated average rectifier current at $T_A=25^\circ\text{C}$ for 500hrs.	MIL-STD-750D METHOD-1027
5. Intermittent Operation Life	$T_A = 25^\circ\text{C}$, $I_F = I_O$ On state: power on for 5 min. off state: power off for 5 min. on and off for 500 cycles.	MIL-STD-750D METHOD-1036
6. Pressure Cooker	$15P_{SIG}$ at $T_A=121^\circ\text{C}$ for 4 hrs.	JESD22-A102
7. Temperature Cycling	-55°C to +125°C dwelled for 30 min. and transferred for 5min. total 10 cycles.	MIL-STD-750D METHOD-1051
8. Forward Surge	Peak Forward Current	MIL-STD-750D METHOD-4066-2
9. Humidity	at $T_A=85^\circ\text{C}$, RH=85% for 1000hrs.	MIL-STD-750D METHOD-1021
10. High Temperature Storage Life	at 175°C for 1000 hrs.	MIL-STD-750D METHOD-1031